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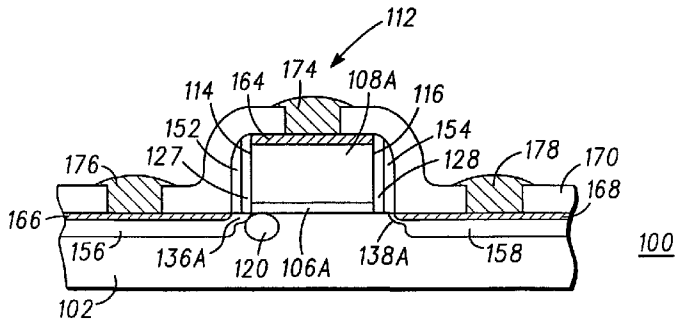
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(54) Title: SEMICONDUCTOR COMPONENT AND METHOD OF MANUFACTURE



(57) Abstract: An insulated gate field effect semiconductor component (100) having a source-side halo region (120) and a method for manufacturing the semiconductor component (100). A gate structure (112) is formed on a semiconductor substrate (102). The source-side halo region (120) is formed in the semiconductor substrate (102). After formation of the source-side halo region (120), spacers (127, 128, 152, 154) are formed adjacent opposing sides of the gate structure (112). A source extension region (136A) and a drain extension region (138A) are formed in the semiconductor substrate (102) using an angled implant. The source extension region (136A) extends under the gate structure (112), whereas the drain extension region (138A) may extend under the gate structure (112) or be laterally spaced apart from the gate structure (112). A source region (156) and a drain region (158) are formed in the semiconductor substrate (102).

WO 2004/040655 A2